

**SURFACE MOUNT GLASS PASSIVATED
 SUPER FAST SILICON RECTIFIER**
VOLTAGE RANGE 50 to 400 Volts CURRENT 1.0 Ampere

FEATURES

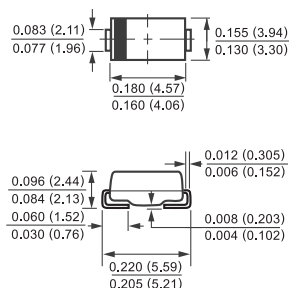
- * Glass passivated device
- * Ideal for surface mounted applications
- * Low leakage current
- * Metallurgically bonded construction
- * Mounting position: Any
- * Weight: 0.09 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.



DO-214AA



Dimensions in inches and (millimeters)

MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	EFMB101	EFMB102	EFMB103	EFMB104	EFMB105	EFMB106	UNITS
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	150	200	300	400	Volts
Maximum RMS Volts	V _{RMS}	35	70	105	140	210	280	Volts
Maximum DC Blocking Voltage	V _{DC}	50	100	150	200	300	400	Volts
Maximum Average Forward Current at TA = 55°C	I _O	1.0						Amps
Peak Forward Surge Current I _{FM} (surge): 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	I _{FSM}	30						Amps
Typical Junction Capacitance (Note 2)	C _J	15				10		pF
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to + 175						°C

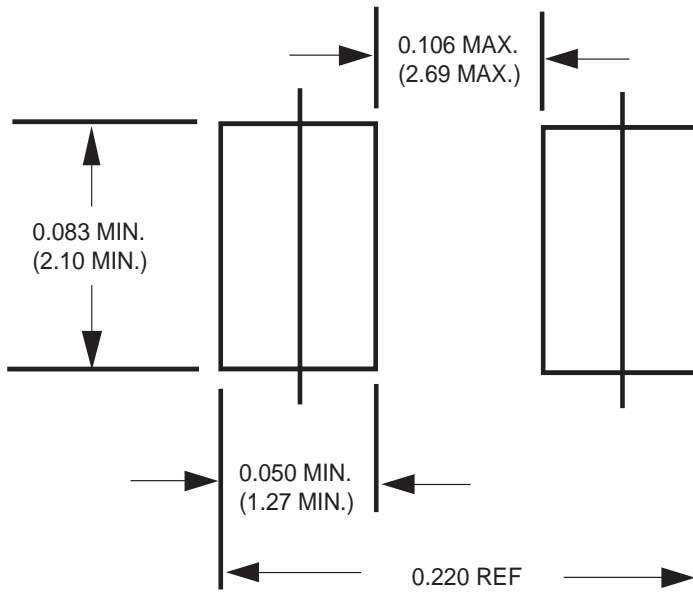
ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	EFMB101	EFMB102	EFMB103	EFMB104	EFMB105	EFMB106	UNITS
Maximum Forward Voltage at 1.0A DC	V _F	0.95			1.25			Volts
Maximum DC Reverse Current	I _R	@ TA = 25°C			5.0			uAmps
at Rated DC Blocking Voltage		@ TA = 150°C			50			
Maximum Reverse Recovery Time (Note 1)	t _{rr}	35						nSec

NOTES : 1. Test Conditions: I_F=0.5A, I_R=1.0A, I_{RR}=0.25A.

2. Measured at 1 MHz and applied reverse voltage of 4.0 volts.

Mounting Pad Layout



Dimensions in inches and (millimeters)